



BYC8X-600P

Hyperfast power diode

3 August 2015

Product data sheet

1. General description

Hyperfast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Isolated plastic package
- Low leakage current
- Low reverse recovery current
- Low thermal resistance
- Reduces switching losses in associated MOSFET

3. Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Half-bridge/full-bridge switched-mode power supplies

4. Quick reference data

Table 1. Quick reference data

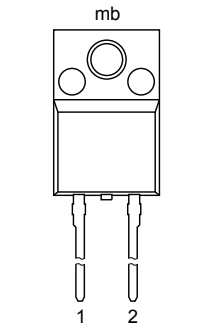
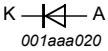
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-------------------------------|-------------------------------------|--|-----|-----|-----|------|
| V_{RRM} | repetitive peak reverse voltage | | - | - | 600 | V |
| $I_{F(AV)}$ | average forward current | $\delta = 0.5$; $T_h \leq 75$ °C; square-wave pulse; Fig. 1 ; Fig. 2 ; Fig. 3 | - | - | 8 | A |
| I_{FRM} | repetitive peak forward current | $\delta = 0.5$; $t_p = 25$ μ s; $T_h \leq 75$ °C; square-wave pulse | - | - | 16 | A |
| I_{FSM} | non-repetitive peak forward current | $t_p = 10$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; Fig. 4 | - | - | 91 | A |
| | | $t_p = 8.3$ ms; $T_{j(init)} = 25$ °C; sine-wave pulse; Fig. 4 | - | - | 100 | A |
| Static characteristics | | | | | | |
| V_F | forward voltage | $I_F = 8$ A; $T_j = 25$ °C; Fig. 6 | - | - | 3.4 | V |
| | | $I_F = 8$ A; $T_j = 125$ °C; Fig. 6 | - | 1.5 | 1.9 | V |
| | | $I_F = 8$ A; $T_j = 150$ °C | - | 1.4 | - | V |



| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-----------------------|---|-----|-----|-----|------|
| Dynamic characteristics | | | | | | |
| t_{rr} | reverse recovery time | $I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7 | - | 12 | 18 | ns |
| | | $I_F = 8\text{ A}$; $V_R = 400\text{ V}$; $di_F/dt = 500\text{ A}/\mu\text{s}$; $T_j = 25\text{ }^\circ\text{C}$; Fig. 7 | - | 19 | - | ns |

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------------------|--|--|
| 1 | K | cathode |  <p>TO-220F (SOD113)</p> |  <p>001aaa020</p> |
| 2 | A | anode | | |
| mb | n.c. | mounting base; isolated | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | |
|-------------|---------|---|---------|
| | Name | Description | Version |
| BYC8X-600P | TO-220F | plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack" | SOD113 |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| BYC8X-600P | BYC8X-600P |

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|--------------------|-------------------------------------|--|-----|-----|------|
| V _{RRM} | repetitive peak reverse voltage | | - | 600 | V |
| V _{RWM} | crest working reverse voltage | | - | 600 | V |
| V _R | reverse voltage | DC | - | 600 | V |
| I _{F(AV)} | average forward current | δ = 0.5 ; T _h ≤ 75 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3 | - | 8 | A |
| I _{FRM} | repetitive peak forward current | δ = 0.5 ; t _p = 25 μs; T _h ≤ 75 °C; square-wave pulse | - | 16 | A |
| I _{FSM} | non-repetitive peak forward current | t _p = 10 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4 | - | 91 | A |
| | | t _p = 8.3 ms; T _{j(init)} = 25 °C; sine-wave pulse; Fig. 4 | - | 100 | A |
| T _{stg} | storage temperature | | -65 | 175 | °C |
| T _j | junction temperature | | - | 175 | °C |

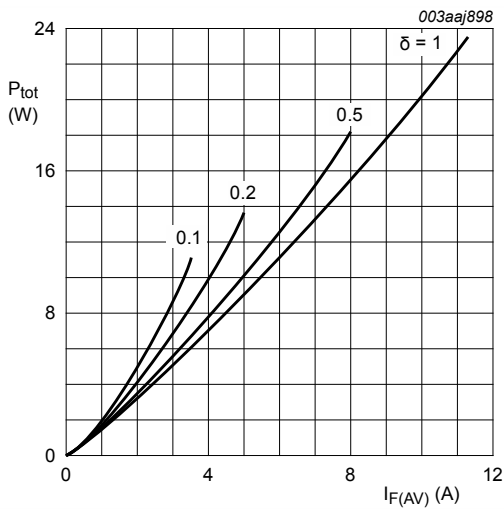


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

$$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$$

V_O = 1.581 V; R_S = 0.043 Ω

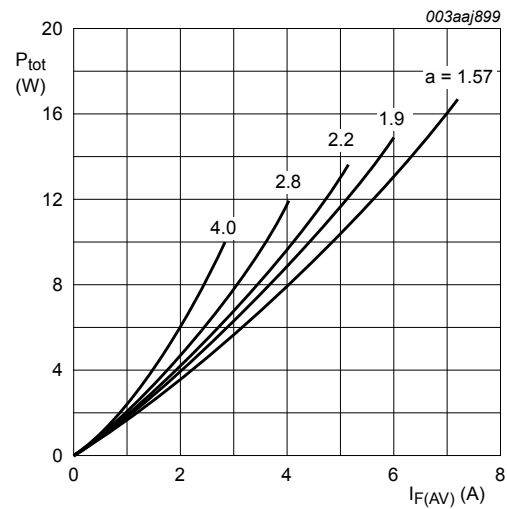


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values

a = form factor = I_{F(RMS)} / I_{F(AV)}

V_O = 1.581 V; R_S = 0.043 Ω

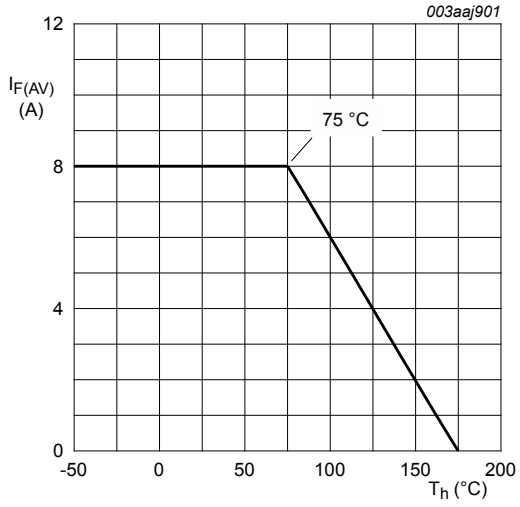


Fig. 3. Average forward current as a function of heatsink temperature; maximum values

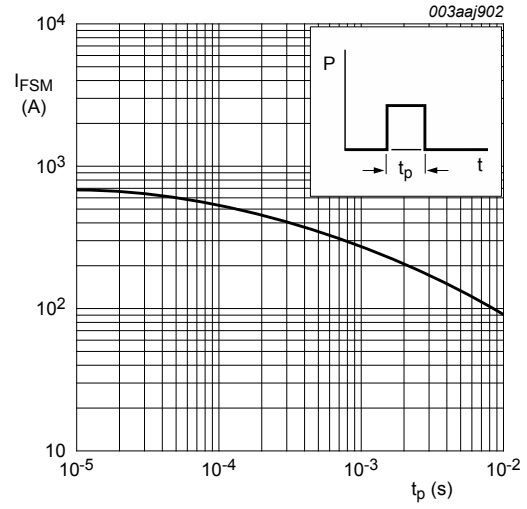


Fig. 4. Non-repetitive peak forward current as a function of pulse width; square waveform; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|---------------|--|--|-----|-----|-----|------|
| $R_{th(j-h)}$ | thermal resistance from junction to heatsink | without heatsink compound | - | - | 7.2 | K/W |
| | | with heatsink compound; Fig. 5 | - | - | 5.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient free air | | - | 60 | - | K/W |

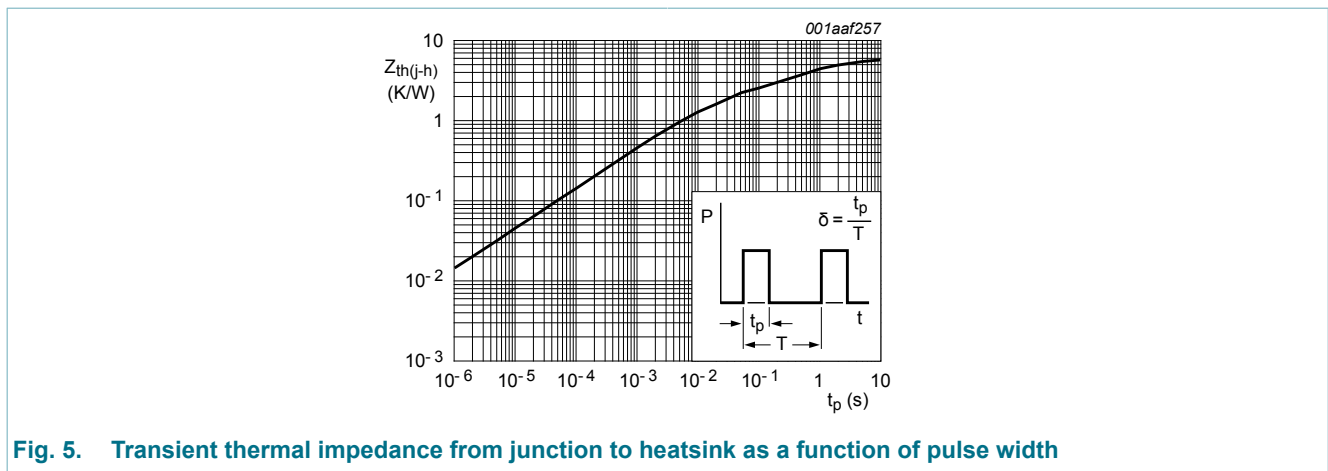


Fig. 5. Transient thermal impedance from junction to heatsink as a function of pulse width

10. Isolation characteristics

Table 7. Isolation characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|-----------------|-----------------------|--|-----|-----|------|------|
| $V_{isol(RMS)}$ | RMS isolation voltage | 50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free | - | - | 2500 | V |
| C_{isol} | isolation capacitance | from cathode to external heatsink | - | 10 | - | pF |

11. Characteristics

Table 8. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|-------------------------------|---|-----|-----|-----|---------------|
| Static characteristics | | | | | | |
| V_F | forward voltage | $I_F = 8\text{ A}$; $T_j = 25\text{ °C}$; Fig. 6 | - | - | 3.4 | V |
| | | $I_F = 8\text{ A}$; $T_j = 125\text{ °C}$; Fig. 6 | - | 1.5 | 1.9 | V |
| | | $I_F = 8\text{ A}$; $T_j = 150\text{ °C}$ | - | 1.4 | - | V |
| I_R | reverse current | $V_R = 600\text{ V}$; $T_j = 25\text{ °C}$ | - | - | 20 | μA |
| | | $V_R = 600\text{ V}$; $T_j = 125\text{ °C}$ | - | - | 200 | μA |
| Dynamic characteristics | | | | | | |
| Q_r | recovered charge | $I_F = 8\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 17 | - | nC |
| | | $I_F = 8\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7 | - | 90 | - | nC |
| t_{rr} | reverse recovery time | $I_F = 1\text{ A}$; $V_R = 30\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 12 | 18 | ns |
| | | $I_F = 8\text{ A}$; $V_R = 400\text{ V}$; $di_F/dt = 500\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | 19 | - | ns |
| I_{RM} | peak reverse recovery current | $I_F = 8\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 25\text{ °C}$; Fig. 7 | - | - | 2.2 | A |
| | | $I_F = 8\text{ A}$; $V_R = 200\text{ V}$; $di_F/dt = 200\text{ A}/\mu\text{s}$; $T_j = 125\text{ °C}$; Fig. 7 | - | - | 6 | A |

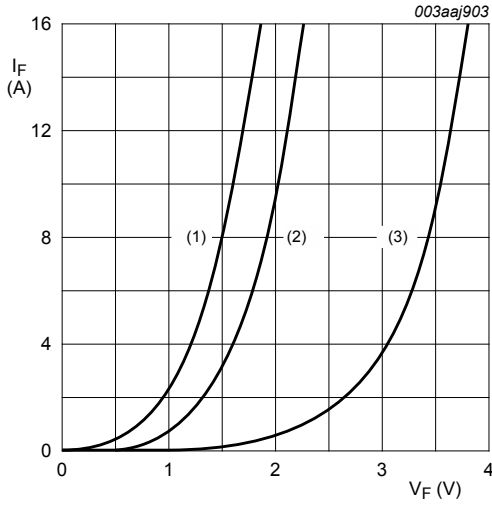


Fig. 6. Forward current as a function of forward voltage

- (1) $T_j = 125\text{ °C}$; typical values;
 - (2) $T_j = 125\text{ °C}$; maximum values;
 - (3) $T_j = 25\text{ °C}$; maximum values;
- $V_O = 1.581\text{ V}$; $R_S = 0.043\text{ }\Omega$

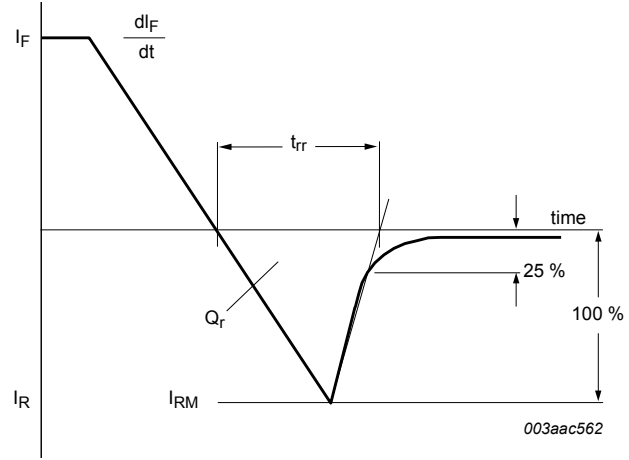
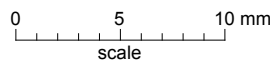
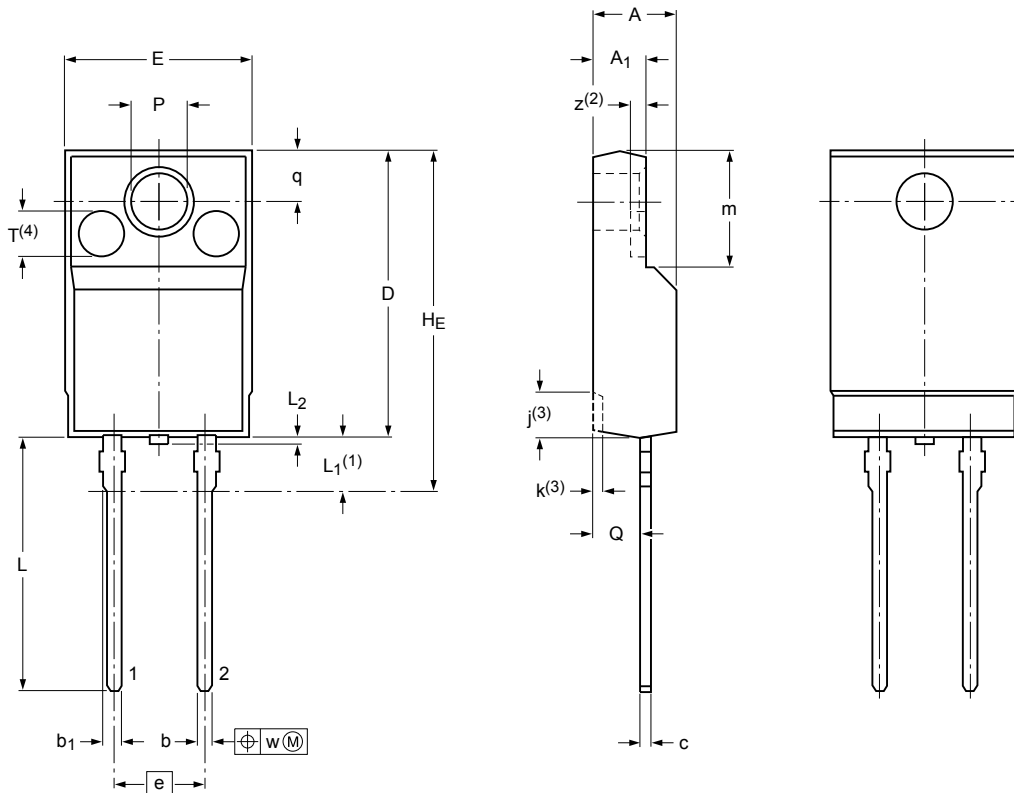


Fig. 7. Reverse recovery definitions; ramp recovery

12. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 'full pack'

SOD113



Dimensions (mm are the original dimensions)

| Unit | A | A ₁ | b | b ₁ | c | D | E | e | H _E max | j ⁽³⁾ | k ⁽³⁾ | L | L ₁ ⁽¹⁾ | L ₂ max | m | P | Q | q | T ⁽⁴⁾ | w | z ⁽²⁾ | |
|------|-----|----------------|-----|----------------|-----|------|------|------|-----------------------|------------------|------------------|------|-------------------------------|-----------------------|-----|-----|-----|---|------------------|------|------------------|-----|
| max | 4.6 | 2.9 | 0.9 | 1.1 | 0.7 | 15.8 | 10.3 | | | 2.7 | 0.6 | 14.4 | 3.3 | | 6.5 | 3.2 | 2.6 | | | | | |
| nom | | | | | | | | 5.08 | 19.0 | | | | | 0.5 | | | | | 2.6 | 2.55 | 0.4 | 0.8 |
| min | 4.0 | 2.5 | 0.7 | 0.9 | 0.4 | 15.2 | 9.7 | | | 1.7 | 0.4 | 13.5 | 2.8 | | 6.3 | 3.0 | 2.3 | | | | | |

Notes

1. Terminals are uncontrolled within zone L1.
2. z is depth of T.
3. Dot lines area designs may vary.
4. Eject pin mark is for reference only.

sod113_po

| Outline version | References | | | | European projection | Issue date |
|-----------------|----------------|-------|-------|--|---------------------|------------------------|
| | IEC | JEDEC | JEITA | | | |
| SOD113 | 2-lead TO-220F | | | | | -07-06-08- 15-08-28 |

Fig. 8. Package outline TO-220F (SOD113)

13. Legal information

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|--------------------------------|--------------------|---|
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